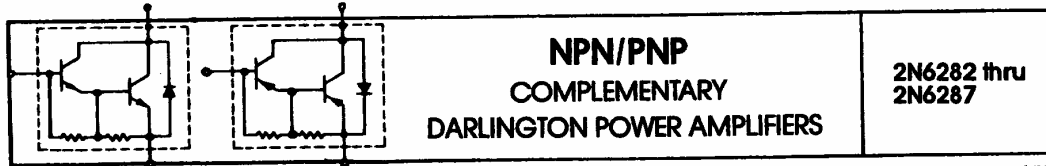


CRYSTALONCS
 2805 Veterans Highway
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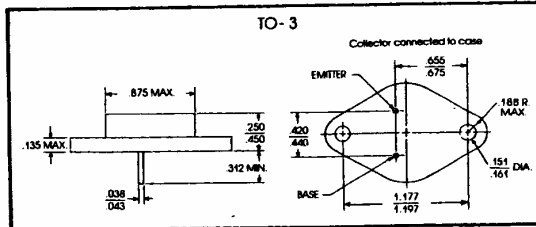


**NPN/PNP
 COMPLEMENTARY
 DARLINGTON POWER AMPLIFIERS**

**2N6282 thru
 2N6287**

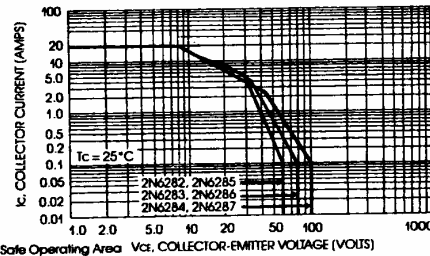
GEOMETRY 509-1

- NPN 2N6282-84
- PNP 2N6285-87
- High Gain
- Monolithic Construction



MAXIMUM RATINGS

PARAMETER	UNIT	2N6282 2N6285	2N6283 2N6286	2N6284 2N6287	UNIT
Collector-Emitter Voltage	V _{CEO}	60	80	100	V
Collector-Base Voltage	V _{CBO}	60	80	100	V
Emitter-Base Voltage	V _{EBO}	5	5	5	V
Collector Current-Continuous		20			A
-Peak		40			A
Base Current		0.5			A
Power Dissipation @ T _C =25°C		160			W
Linear Derating Factor		0.915			W/°C
Storage & Operating Junction Temperature Range		-65°C to +200°C			
Lead Temperature (1/16" from case)		+235°C			



ELECTRICAL CHARACTERISTICS AT 25°C CASE TEMPERATURE

PARAMETER	SYMBOL	TEST CONDITIONS	2N6282 2N6285		2N6283 2N6286		2N6284 2N6287		UNIT
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Collector Cutoff Current (Emitter diode is reverse biased)	I _{CX}	V _{CE} = 60V		5.0					mA
		V _{CE} = 80V				5.0			
		V _{CE} = 100V					5.0		
Collector Cutoff Current (Emitter diode is reverse biased)	I _{CX}	V _{CE} = 60V		0.5					mA
		V _{CE} = 80V				0.5			
		V _{CE} = 100V					0.5		
Emitter Cutoff Current	I _{EBO}	V _{EB} = 5V		2.0		2.0		2.0	mA
Collector-Emitter Open Base* Sustain Voltage	V _{CEO(sus)}	I _B = 0, I _C = 100mA	60		80		100		V
Collector Cutoff Current, Base Open	I _{CEO}	I _B = 0, V _{CE} = 30V		1.0					mA
		I _B = 0, V _{CE} = 40V				1.0 ¹			mA
		I _B = 0, V _{CE} = 50V						1.0	mA
		I _B = 0, V _{CE} = 50V							
DC Forward Current Transfer Ratio*	h _{FE}	I _C = 20A, V _{CE} = 3V	100		100		100		
		I _C = 10A, V _{CE} = 3V	750	18,000	750	18,000	750	18,000	
Collector-Emitter Saturation Voltage*	V _{CE(sat)}	I _C = 20A, I _B = 0.2A		3.0		3.0		3.0	V
		I _C = 10A, I _B = 40mA		2.0		2.0		2.0	V
Base-Emitter Voltage*	V _{BE}	I _C = 10A, V _{CE} = 3V		2.8		2.8		2.8	V
Base-Emitter Saturation Voltage*	V _{BE(sat)}	I _C = 20A, I _B = 200mA		4.0		4.0		4.0	V
High Frequency Beta	h _{fe}	V _{CE} = 3V, I _C = 10A, f = 1MHz	4		4		4		
Low Frequency Beta	h _{fe}	V _{CE} = 3V, I _C = 10A, f = 1kHz	300		300		300		
			2N6282, 2N6283 2N6284		2N6285, 2N6286 2N6287				UNIT
Common Base Output Capacitance	C _{ob}	V _{CB} = 10V, I _E = 0A, f = 0.1MHz	MIN.	MAX.	MIN.	MAX.			
				400		600			pF

*Pulse Width < 300μs; Duty Cycle < 2%